

Low Power, High Precision Operational Amplifier

NP97

FEATURES

Low supply current: 600 μA maximum

OP07 type performance

Offset voltage: 20 μV maximum

Offset voltage drift: 0.6 μV/°C maximum

Very low bias current 25°C: 100 pA maximum

-55°C to +125°C: 250 pA maximum

High common-mode rejection: 114 dB minimum

Extended industrial temperature range: -40°C to +85°C

GENERAL DESCRIPTION

The OP97 is a low power alternative to the industry-standard OP07 precision amplifier. The OP97 maintains the standards of performance set by the OP07 while utilizing only 600 μA supply current, less than 1/6 that of an OP07. Offset voltage is an ultralow 25 μV , and drift over temperature is below 0.6 $\mu V/^{\circ}C$. External offset trimming is not required in the majority of circuits.

Improvements have been made over OP07 specifications in several areas. Notable is bias current, which remains below 250 pA over the full military temperature range. The OP97 is ideal for use in precision long-term integrators or sample-and-hold circuits that must operate at elevated temperatures.

PIN CONNECTIONS

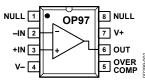


Figure 1. 8-Lead PDIP (P Suffix) 8-Lead SOIC (S Suffix)

Common-mode rejection and power supply rejection are also improved with the OP97, at 114 dB minimum over wider ranges of common-mode or supply voltage. Outstanding PSR, a supply range specified from ±2.25 V to ±20 V, and the minimal power requirements of the OP97 combine to make the OP97 a preferred device for portable and battery-powered instruments.

The OP97 conforms to the OP07 pinout, with the null potentiometer connected between Pin 1 and Pin 8 with the wiper to V+. The OP97 upgrades circuit designs using AD725, OP05, OP07, OP12, and PM1012 type amplifiers. It may replace 741-type amplifiers in circuits without nulling or where the nulling circuitry has been removed.

SPECIFICATIONS

ELECTRICAL CHARACTERISTICS

 $V_S = \pm 15$ V, $V_{CM} = 0$ V, $T_A = 25$ °C, unless otherwise noted.

Table 1.

				OP97E			OP97F		
Parameter	Symbol	Conditions	Min	Тур	Max	Min	Тур	Max	Unit
INPUT CHARACTERISTICS									
Input Offset Voltage	Vos			10	25		30	75	μV
Long-Term Offset									
Voltage Stability	ΔV_{OS} /Time			0.3			0.3		μV/month
Input Offset Current	los			30	100		30	150	pА
Input Bias Current	I _B			±30	±100		±30	±150	рА
Input Noise Voltage	e _n p-p	0.1 Hz to 10 Hz		0.5			0.5		μV p-p
Input Noise Voltage Density	e _n	$f_0 = 10 \text{ Hz}^1$		17	30		17	30	nV/√Hz
		$f_0 = 1000 \text{ Hz}^2$		14	22		14	22	nV/√Hz
Input Noise Current Density	İn	$f_0 = 10 \text{ Hz}$		20			20		fA/√Hz
Large Signal Voltage Gain	Avo	$V_0 = \pm 10 \text{ V}; R_L = 2 \text{ k}\Omega$	300	2000		200	2000		V/mV
Common-Mode Rejection	CMR	$V_{CM} = \pm 13.5 \text{ V}$	114	132		110	132		dB
Input Voltage Range ³	IVR		±13.5	±14.0		±13.5	±14.0		V
OUTPUT CHARACTERISTICS									
Output Voltage Swing	Vo	$R_L = 10 \text{ k}\Omega$	±13	±14		±13	±14		V
Differential Input Resistance ⁴	R _{IN}		30			30			ΜΩ
POWER SUPPLY									
Power Supply Rejection	PSR	$V_S = \pm 2 \text{ V to } \pm 20 \text{ V}$	114	132		110	132		dB
Supply Current	Isy			380	600		380	600	μΑ
Supply Voltage	Vs	Operating range	±2	±15	±20	±2	±15	±20	V
DYNAMIC PERFORMANCE									
Slew Rate	SR		0.1	0.2		0.1	0.2		V/µs
Closed-Loop Bandwidth	BW	$A_{VCL} = 1$	0.4	0.9		0.4	0.9		MHz

¹ 10 Hz noise voltage density is sample tested. Devices 100% tested for noise are available on request.

² Sample tested. ³ Guaranteed by CMR test. ⁴ Guaranteed by design.

OP97

 $V_S = \pm 15$ V, $V_{CM} = 0$ V, -40 °C $\leq T_A \leq +85$ °C for the OP97E/OP97F, unless otherwise noted.

Table 2.

				OP97E			OP97F		
Parameter	Symbol	Conditions	Min	Тур	Max	Min	Тур	Max	Unit
Input Offset Voltage	Vos			25	60		60	200	μV
Average Temperature	TCVos	S suffix		0.2	0.6		0.3	2.0	μV/°C
Coefficient of Vos							0.3		
Input Offset Current	los			60	250		80	750	рА
Average Temperature	TClos			0.4	2.5		0.6	7.5	pA/°C
Coefficient of los									
Input Bias Current	I _B			±60	±250		±80	±750	рА
Average Temperature									
Coefficient of I _B	TCI _B			0.4	2.5		0.6	7.5	pA/°C
Large Signal Voltage Gain	A _{VO}	$V_0 = 10 \text{ V}; R_L = 2 \text{ k}\Omega$	200	1000		150	1000		V/mV
Common-Mode Rejection	CMR	$V_{CM} = \pm 13.5 \text{ V}$	108	128		108	128		dB
Power Supply Rejection	PSR	$V_S = \pm 2.5 \text{ V to } \pm 20 \text{ V}$	108	126		108	128		dB
Input Voltage Range ¹	IVR		±13.5	±14.0		±13.5	±14.0		٧
Output Voltage Swing	Vo	$R_L = 10 \text{ k}\Omega$	±13	±14		±13	±14		٧
Slew Rate	SR		0.05	0.15		0.05	0.15		V/µs
Supply Current	I _{SY}			400	800		400	800	μΑ
Supply Voltage	Vs	Operating range	±2.5	±15	±20	±2.5	±15	±20	٧

¹ Guaranteed by CMR test.

ABSOLUTE MAXIMUM RATINGS

Absolute maximum ratings apply to both DICE and packaged parts, unless otherwise noted.

Table 3.

Parameter	Rating
Supply Voltage	±20 V
Input Voltage ¹	±20 V
Differential Input Voltage ²	±1 V
Differential Input Current ²	±10 mA
Output Short-Circuit Duration	Indefinite
Operating Temperature Range	−40°C to +85°C
OP97E, OP97F (P, S)	
Storage Temperature Range	−65°C to +150°C
Junction Temperature Range	−65°C to +150°C
Lead Temperature (Soldering, 60 sec)	300°C

 $^{^1\}mbox{For supply voltages}$ less than ± 20 V, the absolute maximum input voltage is equal to the supply voltage.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

THERMAL RESISTANCE

 θ_{JA} is specified for the worst-case conditions, that is, a device soldered in a circuit board for surface-mount packages.

Table 4.

	Package Type	θ_{JA}^1	Ө лс	Unit
_	8-Lead PDIP (P Suffix)	103	43	°C/W
	8-Lead SOIC (S Suffix)	158	43	°C/W

 $^{^{1}}$ θ_{JA} is specified for worst-case mounting conditions, that is, θ_{JA} is specified for device in socket for PDIP package; θ_{JA} is specified for device soldered to printed circuit board for SOIC package.

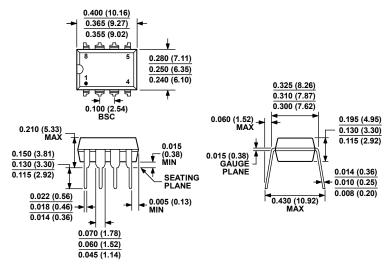
ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

² The inputs of the OP97 are protected by back-to-back diodes. Current-limiting resistors are not used in order to achieve low noise. Differential input voltages greater than 1 V cause excessive current to flow through the input protection diodes unless limiting resistance is used.

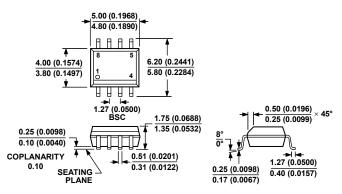
OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MS-001

CONTROLLING DIMENSIONS ARE IN INCHES; MILLIMETER DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF INCH EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN. CORNER LEADS MAY BE CONFIGURED AS WHOLE OR HALF LEADS.

Figure 41. 8-Lead Plastic Dual In-Line Package [PDIP]
P-Suffix
(N-8)
Dimensions shown in inches and (millimeters)



COMPLIANT TO JEDEC STANDARDS MS-012-AA

CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 42. 8-Lead Standard Small Outline Package [SOIC]

Narrow Body

S-Suffix

(R-8)

Dimensions shown in millimeters and (inches)

OP97

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option
OP97EP	-40°C to +85°C	8-Lead PDIP	N-8
OP97EPZ ¹	-40°C to +85°C	8-Lead PDIP	N-8
OP97FP	-40°C to +85°C	8-Lead PDIP	N-8
OP97FPZ ¹	-40°C to +85°C	8-Lead PDIP	N-8
OP97FS	-40°C to +85°C	8-Lead SOIC	R-8
OP97FS-REEL	-40°C to +85°C	8-Lead SOIC	R-8
OP97FS-REEL7	-40°C to +85°C	8-Lead SOIC	R-8
OP97FSZ ¹	-40°C to +85°C	8-Lead SOIC	R-8
OP97FSZ-REEL ¹	-40°C to +85°C	8-Lead SOIC	R-8
OP97FSZ-REEL7 ¹	−40°C to +85°C	8-Lead SOIC	R-8

 $^{^{1}}$ Z = RoHS Compliant Part.

